

Amendments to the Claims:

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

1. (Currently Amended) A semiconductor device, comprising:
 - a drain electrode;
 - a source electrode;
 - a channel contacting the drain electrode and the source electrode, wherein the channel includes one or more compounds of the formula $A_xB_xO_x$, wherein the one or more compounds of the formula $A_xB_xO_x$ includes one or more of gallium-germanium oxide, gallium-tin oxide, gallium-lead oxide, indium-germanium oxide, indium-lead oxide ~~wherein each A is selected from the group of Ga, In, each B is selected from the group of Ge, Sn, Pb~~, each O is atomic oxygen, each x is independently a non-zero number, wherein the channel includes one of an amorphous form and a mixed-phase crystalline form; and
 - a gate dielectric positioned between a gate electrode and the channel.
2. (Currently Amended) The semiconductor device of claim 1, wherein the one or more compounds of the formula $A_xB_xO_x$ includes an atomic composition of metal (A)-to-metal (B) ratio of A:B, wherein proportions of A, and B, based on stoichiometric x values associated with A, and B, are each in a range of about 0.05 to about 0.95.
3. (Canceled)
4. (Canceled)

5. (Canceled)

6. (Previously Presented) The semiconductor device of claim 1, wherein the one or more compounds of the formula $A_xB_xO_x$ includes C_x to form a compound of the formula $A_xB_xC_xO_x$, wherein each C is selected from the group of Ga, In, Ge, Sn, Pb, each O is atomic oxygen, each x is independently a non-zero number, and wherein each of A, B, and C are different.

7. (Currently Amended) The semiconductor device of claim 6, wherein the one or more compounds of the formula $A_xB_xC_xO_x$ includes an atomic composition of metal (A)-to-metal (B)-to-metal (C) ratio of A:B:C, wherein proportions of A, B, and C, based on stoichiometric x values associated with A, B, and C, are each in a range of about 0.025 to about 0.95.

8. (Previously Presented) The semiconductor device of claim 1, wherein the one or more compounds of the formula $A_xB_xC_xO_x$ includes one or more of gallium-germanium-tin oxide, gallium-tin-lead oxide, gallium-germanium-lead oxide, gallium-indium-germanium oxide, gallium-indium-tin oxide, gallium-indium-lead oxide, indium-germanium-tin oxide, indium-tin-lead oxide, indium-germanium-lead oxide.

9. (Currently Amended) The semiconductor device of claim 8, wherein the one or more compounds of the formula $A_xB_xC_xO_x$ includes an atomic composition of metal (A)-to-metal (B)-to-metal (C) ratio A:B:C, wherein proportions of A, B, and C, based on stoichiometric x values associated with A, B, and C, are each in a range of about 0.025 to about 0.95.

10. (Previously Presented) The semiconductor device of claim 6, wherein the one or more compounds of formula $A_xB_xC_xO_x$, includes D_x , to form a compound of the formula

$A_xB_xC_xD_xO_x$, wherein each D is selected from the group of Ga, In, Ge, Sn, Pb, each O is atomic oxygen, each x is independently a non-zero number, and wherein each of A, B, C, and D are different.

11. (Currently Amended) The semiconductor device of claim 10, wherein the one or more compounds of the formula $A_xB_xC_xD_xO_x$ includes an atomic composition of metal (A)-to-metal (B)-to-metal (C)-to-metal (D) ratio of A:B:C:D, wherein proportions of A, B, C, and D, based on stoichiometric x values associated with A, B, C, and D, are each in a range of about 0.017 to about 0.95.

12. (Previously Presented) The semiconductor device of claim 1, wherein the one or more compounds of the formula $A_xB_xC_xD_xO_x$ includes one or more of gallium-germanium-tin-lead oxide, gallium-indium-germanium-tin oxide, gallium-indium-germanium-lead oxide, gallium-indium-tin-lead oxide, indium-germanium-tin-lead oxide.

13. (Currently Amended) The semiconductor device of claim 12, wherein the one or more compounds of the formula $A_xB_xC_xD_xO_x$ includes an atomic composition of metal (A)-to-metal (B)-to-metal (C)-to-metal (D) ratio A:B:C:D, wherein proportions of A, B, C, and D, based on stoichiometric x values associated with A, B, C, and D, are each in a range of about 0.017 to about 0.95.

14. (Previously Presented) The semiconductor device of claim 10, wherein the one or more compounds of formula $A_xB_xC_xD_xO_x$ includes E_x , to form a compound of the formula $A_xB_xC_xD_xE_xO_x$, wherein each E is selected from the group of Ga, In, Ge, Sn, Pb, each O is atomic oxygen, each x is independently a non-zero number, and wherein each of A, B, C, D, and E are different.

15. (Currently Amended) The semiconductor device of claim 14, wherein the one or more compounds of the formula $A_xB_xC_xD_xE_xO_x$ includes an atomic composition of metal (A)-to-metal (B)-to-metal (C)-to-metal (D) ratio of A:B:C:D:E, wherein proportions of A, B, C, D, and E, based on stoichiometric x values associated with A, B, C, D and E, are each in a range of about 0.013 to about 0.95.

16. (Previously Presented) The semiconductor device of claim 1, wherein the one or more compounds of the formula $A_xB_xC_xD_xE_xO_x$ includes one or more of gallium-indium-germanium-tin-lead oxide.

17. (Currently Amended) The semiconductor device of claim 16, wherein the gallium-indium-germanium-tin-lead oxide includes an atomic composition of metal (A)-to-metal (B)-to-metal (C)-to-metal (D)-to-metal (E) ratio A:B:C:D:E, wherein proportions of A, B, C, D, and E, based on stoichiometric x values associated with A, B, C, D and E, are each in a range of about 0.013 to about 0.95.

18. (Currently Amended) A semiconductor device, comprising:
a drain electrode;
a source electrode;
means for controlling current flow electrically coupled to the drain electrode and the source electrode, wherein the means for controlling current flow includes one or more compounds of the formula $A_xB_xO_x$, wherein the one or more compounds of the formula $A_xB_xO_x$ includes one or more of gallium-germanium oxide, gallium-tin oxide, gallium-lead oxide, indium-germanium oxide, indium-lead oxide ~~wherein each A is selected from the group of Ga, In, each B is selected from the group of Ge, Sn, Pb,~~ each x is independently a non-zero number, wherein the channel includes one of an amorphous form and a mixed-phase crystalline form; and
a gate electrode separated from a channel by a gate dielectric.

19. (Canceled)
20. (Original) The semiconductor device of claim 18, wherein the source, drain, and gate electrodes include a substantially transparent material.
21. (Withdrawn) A method of forming a channel, comprising:
providing at least one precursor composition including one or more precursor compounds that include A_x , and one or more compounds that include B_x , wherein each A is selected from the group of Ga, In, each B is selected from the group Ge, Sn, Pb, each x is independently a non-zero integer, and wherein each of A and B are different; and
depositing the channel including the precursor composition to form a multicomponent oxide from the precursor composition to electrically couple a drain electrode and a source electrode.
22. (Withdrawn) The method of claim 21, including providing a substrate or substrate assembly; and
forming the semiconductor device on the substrate or substrate assembly.
23. (Withdrawn) The method of claim 21, wherein depositing the channel includes depositing one of an amorphous form, a single-phase crystalline form, and a mixed-phase crystalline form.
24. (Withdrawn) The method of claim 21, wherein the precursor composition includes a liquid form.
25. (Withdrawn) The method of claim 24, wherein depositing the channel includes an ink-jet deposition technique when the precursor composition includes the liquid form.

26. (Withdrawn) The method of claim 21, wherein the one or more precursor compounds includes one or more precursor compounds that include C_x , wherein each C is selected from the group of Ga, In, Ge, Sn, Pb, each x is independently a non-zero integer, and wherein each of A, B, and C are different.

27. (Withdrawn) The method of claim 26, wherein the one or more precursor compounds includes one or more precursor compounds that include D_x , wherein each D is selected from the group of Ga, In, Ge, Sn, Pb, each x is independently a non-zero integer, and wherein each of A, B, C, and D are different.

28. (Withdrawn) The method of claim 27, wherein the one or more precursor compounds includes one or more precursor compounds that include E_x , wherein E is selected from the group of Ga, In, Ge, Sn, Pb, each x is independently a non-zero integer, and wherein each of A, B, C, D, and E are different.

29. (Withdrawn) The method of claim 28, wherein depositing a channel includes a step for vaporizing the precursor composition to form a vaporized precursor composition, and depositing the vaporized precursor composition using a physical vapor deposition technique including one or more of dc reactive sputtering, rf sputtering, magnetron sputtering, ion beam sputtering.

30. (Withdrawn) A method of manufacturing a semiconductor device, comprising:
providing a drain electrode;
providing a source electrode;
step for providing a precursor composition including one or more precursor compounds that include A_x , and one or more compounds that include B_x , wherein each A is selected from the group of Ga, In, each B is selected from the group Ge, Sn, Pb, each x is independently a non-zero integer, and wherein each of A and B are different;

step for depositing a channel including depositing the precursor composition to form a multicomponent oxide from the precursor composition to electrically couple the drain electrode and the source electrode;

providing a gate electrode; and

providing a gate dielectric positioned between the gate electrode and the channel.

31. (Withdrawn) The method of claim 30, wherein providing the source, the drain, and the gate electrodes includes providing a substantially transparent form of the source, the drain, and the gate electrodes.

32. (Withdrawn) The method of claim 30, wherein the one or more precursor compounds includes one or more precursor compounds that include C_x , wherein each C is selected from the group of Ga, In, Ge, Sn, Pb, each x is independently a non-zero integer, and wherein each of A, B, and C are different.

33. (Withdrawn) The method of claim 32, wherein the one or more precursor compounds includes one or more precursor compounds that include D_x , wherein each D is selected from the group of Ga, In, Ge, Sn, Pb, each x is independently a non-zero integer, and wherein each of A, B, C, and D are different.

34. (Withdrawn) The method of claim 33, wherein the one or more precursor compounds includes one or more precursor compounds that include E_x , wherein each E is selected from the group of Ga, In, Ge, Sn, Pb, each x is independently a non-zero integer, and wherein each of A, B, C, D, and E are different.

35. (Withdrawn) The method of claim 34, wherein the step for depositing a channel includes a step for vaporizing the precursor composition to form a vaporized precursor composition, and depositing the vaporized precursor composition using a physical vapor

deposition technique including one or more of dc reactive sputtering, rf sputtering, magnetron sputtering, ion beam sputtering.

36. (Withdrawn) The method of claim 34, wherein the step for depositing a channel includes an ink-jet deposition technique.

37. (Currently Amended) A semiconductor device formed by the steps, comprising:
providing a drain electrode;

providing a source electrode;

providing a precursor composition including one or more precursor compounds that include A_x and one or more compounds that include B_x , wherein the one or more compounds of the formula $A_xB_xO_x$ includes one or more of gallium-germanium oxide, gallium-tin oxide, gallium-lead oxide, indium-germanium oxide, indium-lead oxide ~~wherein each A is selected from the group of Ga, In, each B is selected from the group of Ge, Sn, Pb,~~ each x is independently a non-zero number, wherein the channel includes one of an amorphous form and a mixed-phase crystalline form;

depositing a channel including the precursor composition to form a multicomponent oxide from the precursor composition to electrically couple the drain electrode and the source electrode;

providing a gate electrode; and

providing a gate dielectric positioned between the gate electrode and the channel.

38. (Previously Presented) The semiconductor device of claim 37, wherein the one or more precursor compounds includes one or more precursor compounds that include C_x , wherein each C is selected from the group of Ga, In, Ge, Sn, Pb, each x is independently a non-zero number, and wherein each of A, B, and C are different.

39. (Previously Presented) The semiconductor device of claim 38, wherein the one or more precursor compounds includes one or more precursor compounds that include D_x , wherein each D is selected from the group of Ga, In, Ge, Sn, Pb, each x is independently a non-zero number, and wherein each of A, B, C, and D are different.

40. (Previously Presented) The semiconductor device of claim 39, wherein the one or more precursor compounds includes one or more precursor compounds that include E_x , wherein each E is selected from the group of Ga, In, Ge, Sn, Pb, each x is independently a non-zero number, and wherein each of A, B, C, D, and E are different.

41. (Original) The semiconductor device of claim 40, wherein depositing the channel includes vaporizing the precursor composition to form a vaporized precursor composition, and depositing the vaporized precursor composition using a physical vapor deposition technique including one or more of dc reactive sputtering, rf sputtering, magnetron sputtering, ion beam sputtering.

42. (Original) The semiconductor device of claim 37, wherein providing the source, the drain, and the gate electrodes includes providing a substantially transparent form of the source, the drain, and the gate electrodes.

43. (Original) The semiconductor device of claim 37, wherein providing the precursor composition includes providing a liquid form of the precursor composition.

44. (Original) The semiconductor device of claim 43, wherein depositing the channel includes an ink-jet deposition technique when the precursor composition includes the liquid form.

45. (Withdrawn) A method for operating a semiconductor device, comprising:

providing a semiconductor device that includes a source electrode a drain electrode, and a channel to electrically couple the source electrode and the drain electrode, a gate electrode separated from the channel by a gate dielectric, wherein the channel includes a multicomponent oxide selected from at least one metal cation from group 13, and at least one metal cation from group 14, wherein group 13 cations include Ga and In, and group 14 cations include Ge, Sn, and Pb, wherein each component in the multicomponent oxide is different; and

applying a voltage to the gate electrode to effect a flow of electrons through the channel.

46. (Withdrawn) The method of claim 45, wherein operating the semiconductor device includes using the semiconductor device as a switch in a display device.

47. (Withdrawn) The method of claim 45, wherein operating the semiconductor device includes conducting electrons through the channel in a linear region of operation.

48. (Currently Amended) A display device, comprising:

a plurality of pixel devices configured to operate collectively to display images, where each of the pixel devices includes a semiconductor device configured to control light emitted by the pixel device, the semiconductor device including:

a drain electrode;

a source electrode;

a channel contacting the drain electrode and the source electrode,

wherein the channel includes one or more compounds of the formula $A_xB_xO_x$,

wherein the one or more compounds of the formula $A_xB_xO_x$ includes one or

more of gallium-germanium oxide, gallium-tin oxide, gallium-lead oxide,

indium-germanium oxide, indium-lead oxide ~~wherein each A is selected from~~

~~the group of Ga, In, each B is selected from the group of Ge, Sn, Pb, each O is~~

atomic oxygen, each x is independently a non-zero number, wherein the channel includes one of an amorphous form and a mixed-phase crystalline form;
a gate electrode; and
a gate dielectric positioned between the gate electrode and the channel and configured to permit application of an electric field to the channel.

49. (Original) The display of claim 48, wherein the source, the drain, and the gate electrodes include a substantially transparent material.

50. (Currently Amended) The display of claim 48, wherein the one or more compounds of the formula $A_xB_xO_x$ includes an atomic composition of metal (A)-to-metal (B) of ratio A:B, wherein proportions of A, and B, based on stoichiometric x values associated with A, and B, are each in a range of about 0.05 to about 0.95.

51. (Previously Presented) The display of claim 48, wherein the one or more compounds of the formula $A_xB_xO_x$ includes C_x , to form a compound of the formula $A_xB_xC_xO_x$, wherein each C is selected from the group of Ga, In, Ge, Sn, Pb, each O is atomic oxygen, each x is independently a non-zero number, and wherein each of A, B, and C are different.

52. (Currently Amended) The display of claim 51, wherein the one or more compounds of the formula $A_xB_xC_xO_x$ includes an atomic composition of metal (A)-to-metal (B)-to-metal (C) ratio A:B:C, wherein proportions of A, B, and C, based on stoichiometric x values associated with A, B, and C, are each in a range of about 0.025 to about 0.95.

53. (Previously Presented) The display of claim 51, wherein the one or more compounds of formula $A_xB_xC_xO_x$, includes D_x , to form a compound of the formula $A_xB_xC_xD_xO_x$, wherein each D is selected from the group of Ga, In, Ge, Sn, Pb, each O is

atomic oxygen, each x is independently a non-zero number, and wherein each of A, B, C, and D are different.

54. (Currently Amended) The display of claim 53, wherein the one or more compounds of the formula $A_xB_xC_xD_xO_x$ includes an atomic composition of metal (A)-to-metal (B)-to-metal (C)-to-metal (D) ratio A:B:C:D, wherein proportions of A, B, C, and D, based on stoichiometric x values associated with A, B, C, and D, are each in a range of about 0.017 to about 0.95.

55. (Previously Presented) The display of claim 53, wherein the one or more compounds of formula $A_xB_xC_xD_xO_x$ includes E_x , to form a compound of the formula $A_xB_xC_xD_xE_xO_x$, wherein each E is selected from the group of Ga, In, Ge, Sn, Pb, each O is atomic oxygen, each x is independently a non-zero number, and wherein each of A, B, C, D, and E are different.

56. (Currently Amended) The display of claim 55, wherein the one or more compounds of the formula $A_xB_xC_xD_xE_xO_x$ includes an atomic composition of metal (A)-to-metal (B)-to-metal (C)-to-metal (D)-to-metal (E) ratio of A:B:C:D:E, wherein proportions of A, B, C, D, and E, based on stoichiometric x values associated with A, B, C, D, and E, are each in a range of about 0.013 to about 0.95.

57. (Canceled)